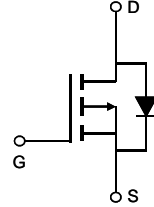




P-channel Enhancement Mode Mosfet

CX3419

The CX3419 uses advanced trench technology to provide excellent RDS(ON) and low gate charge. This device is suitable for use as a load switch or in PWM applications.

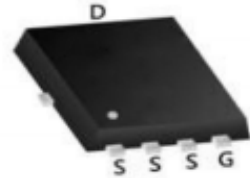


GENERAL FEATURES

- RDS(ON) < 13mΩ @ VGS=-4.5V
RDS(ON) < 9mΩ @ VGS=-10V
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

Application

- PWM applications
- Load switch
- Power management



DFN3X3

ABSOLUTE MAXIMUM RATINGS(TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit	
Common Ratings (Tc=25°C Unless Otherwise Noted)				
V _{GS}	Gate-Source Voltage	±20	V	
V _{(BR)DSS}	Drain-Source Breakdown Voltage	-30	V	
T _J	Maximum Junction Temperature	175	°C	
T _{STG}	Storage Temperature Range	-50 to 150	°C	
I _S	Diode Continuous Forward Current ^①	T _C =25°C	-30	A
I _{DM}	Pulse Drain Current Tested ^①	T _C =25°C	-100	A
I _D	Continuous Drain Current(V _{Gs} =-10V) ^①	T _C =25°C	-20	A